NSN 5961-01-212-8009

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View Online at https://aerobasegroup.com/nsn/5961-01-212-8009 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **End Application:** Satellite communications set, an/wsc- (v) 9 **Mounting Facility Quantity:** 2 **Internal Configuration:** Junction contact **Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 120.0 collector to base voltage/static/emitter open and 120.0 collector-to-emitter substaining voltage, with specified circuit between base and emitter and 95.0 collector-to-emitter substaining voltage, resistance between base and emitter and 75.0 collector-to-emitter, substaining voltage, base open-circuited and 7.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 20.00 amperes collector current, dc and 5.00 amperes base current, dc **Power Rating Per Characteristic:** 140.0 watts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:**

No Fiig:

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Demilitarization: